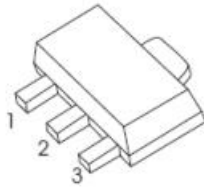


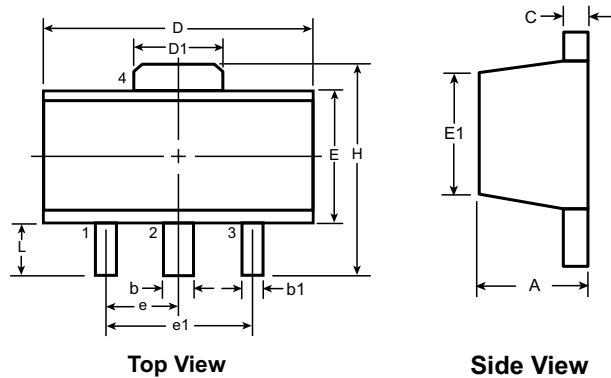
■ Features 特点

PNP Power Amplifier 功率放大

- 1. BASE
- 2. COLLECTOR
- 3. EMITTER



SOT-89 PACKAGE OUTLINE



Symbol	A	b	b1	C	D	D1	E	E1	e	e1	H	L	
Dimensions (mm)	MIN	1.40	0.44	0.36	0.3	4.40	1.50	2.29	2.00 [†]	1.50	3.00	3.94	0.89
	NOM	-	-	-	-	-	-	-	-	BSC	BSC	-	-
	MAX	1.60	0.56	0.48	0.5	4.60	1.75	2.60	2.29	-	-	4.25	1.20

Dimensions in mm

■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V_{CBO}	-40	V
Collector-Emitter Voltage 集电极发射极电压	V_{CEO}	-25	V
Emitter-Base Voltage 发射极基极电压	V_{EBO}	-5	V
Collector Current 集电极电流	I_C	-1500	mA
Power dissipation 耗散功率	$P_C(T_a=25^\circ C)$	500	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	250	$^\circ C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^\circ C$	

SS8550

■Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压($I_C = -100\mu\text{A}$, $I_E = 0$)	BV_{CBO}	-40	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压($I_C = -1\text{mA}$, $I_B = 0$)	BV_{CEO}	-25	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压($I_E = -100\mu\text{A}$, $I_C = 0$)	BV_{EBO}	-5	—	—	V
Collector-Base Leakage Current 集电极基极漏电流($V_{CB} = -40\text{V}$, $I_E = 0$)	I_{CBO}	—	—	-100	nA
Collector-Emitter Punch Throng Current 集电极发射极穿透电流($V_{CE} = -20\text{V}$, $V_{BE} = 0$)	I_{CES}	—	—	-100	nA
Emitter-Base Leakage Current 发射极基极漏电流($V_{EB} = -5\text{V}$, $I_C = 0$)	I_{EBO}	—	—	-100	nA
DC Current Gain 直流电流增益($V_{CE} = -1\text{V}$, $I_C = -100\text{mA}$)	$H_{FE} (1)$	85	—	400	
DC Current Gain 直流电流增益($V_{CE} = -1\text{V}$, $I_C = -800\text{mA}$)	$H_{FE} (2)$	40	—	—	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降 ($I_C = -800\text{mA}$, $I_B = -80\text{mA}$)	$V_{CE(sat)}$	—	—	-0.5	V
Base-Emitter Saturation Voltage 基极发射极饱和压降 ($I_C = -800\text{mA}$, $I_B = -80\text{mA}$)	$V_{BE(sat)}$	—	—	-1.2	V
Transition Frequency 特征频率($V_{CE} = -10\text{V}$, $I_C = -50\text{mA}$)	f_T	100	—	—	MHz
Output Capacitance 输出电容($V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$)	C_{ob}	—	20	—	pF

RATING AND CHARACTERISTIC CURVES (SS8550)

